

**Amendments to the Specification**

Please replace the title as follows:

**THIN FILM MAGNETIC HEAD ~~DEVICE~~ INCLUDING A READING THIN FILM  
MAGNETIC HEAD ELEMENT**

Please replace paragraph [0010] with the following rewritten paragraph:

[0010] In order to realize an extremely narrow record track, the thin film magnetic head element has to be miniaturized. ~~The, the~~ The resistance  $R_H$  of the series resistor 2 is liable to be increased. Particularly, in the tunneling type giant magneto-resistive thin film magnetic head element, the series resistor 2 usually has a high resistance  $R_H$  due to the fact that the current flows perpendicularly to the insulating layer 7, and amounts to several hundreds  $\Omega$  to several  $K\Omega$ . Therefore, the operation frequency range is limited largely. In order to attain the high speed operation by increasing the operation frequency, the output signal is liable to be lowered, and inherent merits of the tunneling type magneto-resistive thin film magnetic head element might be lost.

Please replace paragraph [0015] with the following rewritten paragraph:

[0015] In a preferable embodiment of the thin film magnetic head device according to the invention, a reading thin film magnetic head element formed by a giant magneto-resistive element and a recording thin film magnetic head element formed by an inductive type element are stacked on a substrate. Such a combination type thin film magnetic head device may be advantageously used in a hard disk device having high recording density, large storage capacity and high operation speed. However, according to the invention, the reading thin film magnetic head element is not limited to the giant magneto-resistive element, but may be formed by an anisotropic magneto-resistive element.

**Brief Description of the drawings**

Fig. 1 is an equivalent circuit showing a known thin film magnetic head device

including a tunneling type magneto-resistive element;

Fig. 2 is a perspective view illustrating a principal structure of the tunneling type magneto-resistive element;

Fig. 3 is an equivalent circuit depicting the thin film magnetic head device according to the invention;

Fig. 4 is a graph representing a frequency characteristic of the thin film magnetic head device according to the invention in comparison with a known thin film magnetic head device;

Fig. 5 is a schematic cross sectional view cut along a line perpendicular to an air bearing surface of an embodiment of the thin film magnetic head device according to the invention;

Fig. 6 is a schematic cross sectional view of the ~~tin-film~~thin film magnetic head device shown in Fig. 5 cut along a line parallel with the air bearing surface; and

Fig. 7 is a schematic perspective view depicting the construction of a tunneling type magneto-resistive element provided in the thin film magnetic head device shown in Fig. 6.